

### **INCHANGE SEMICONDUCTOR**

### **isc Silicon NPN Power Transistor**

## 2SD1985A

### DESCRIPTION

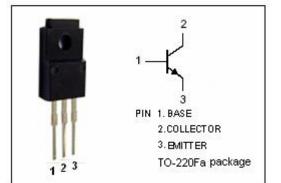
- Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub>= 80V(Min.)
- · Good Linearity of hFE
- Low Collector Saturation Voltage-
- : V<sub>CE(sat)</sub>= 1.2V(Max,)@ I<sub>C</sub>= 3A
- Complement to Type 2SB1393A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

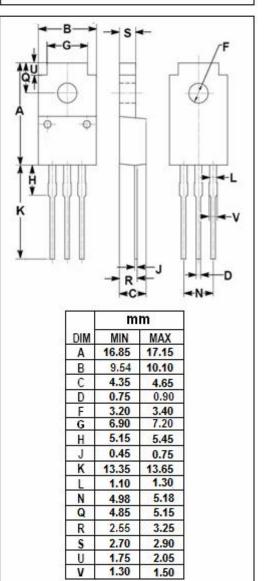
### APPLICATIONS

SYMBOL

Tstg

Designed for high power amplifications.





#### Collector-Base Voltage 80 V V<sub>СВО</sub> Collector-Emitter Voltage VCEO 80 V Emitter-Base Voltage $V_{\text{EBO}}$ 6 V **Collector Current-Continuous** 3 lc А Collector Current-Peak 5 А Ісм **Collector Power Dissipation** 2 @ Ta=25°C W Pc **Collector Power Dissipation** 25 @ Tc=25°C ТJ Junction Temperature 150 °C

VALUE

-55~150

°C

UNIT

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

PARAMETER

isc website: <u>www.iscsemi.com</u>

Storage Temperature Range



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### **ELECTRICAL CHARACTERISTICS**

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	80			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	Ic= 3A; I <sub>B</sub> = 0.375A			1.2	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V			1.8	V
ICES	Collector Cutoff Current	V <sub>CE</sub> = 80V; V <sub>BE</sub> = 0			200	μA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 60V; I <sub>B</sub> = 0			300	μA
I <sub>EBO</sub>	Emitter Cutoff Current	<b>V</b> <sub>EB</sub> <b>=</b> 6 <b>V</b> ; <b>I</b> <sub>C</sub> = 0			1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	70		250	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V	10			
fT	Current-Gain—Bandwidth Product	Ic= 0.1A; Vc== 5 V; f= 1MHz		30		MHz

Switching Times

t <sub>on</sub>	Turn-on Time		0.5	μ <b>S</b>
t <sub>stg</sub>	Storage Time	V <sub>CC</sub> = 50V, I <sub>C</sub> = 1A; I <sub>B1</sub> = I <sub>B2</sub> = 0.1A,	2.5	μ8
tf	Fall Time		0.4	μ8

#### h<sub>FE-1</sub> Classifications

Q	Р		
70-150	120-250		

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